

METHOD FOR PREPARING A THIN LAYER OF FERROELECTRIC MATERIAL

ABSTRACT

The invention relates to a method for preparing a thin single-domain layer (3') of ferroelectric material, the method comprising, between a step of fracturing a donor substrate (1) at a fragilization plane (2) in order to form a first layer (3) and a finishing sequence for the first layer (3), applying a treatment to the free face (8) of the first layer (3) in order to produce a hydrogen concentration that is greater than $2.0 \times 10^{21} \text{ at/cm}^3$ in a surface thickness of the first layer (3).

Figure 3